



PATENT  
8013-1139

IN THE U.S. PATENT AND TRADEMARK OFFICE

In re application of

Atsushi YAMAGUCHI et al.

Conf. 1202

Application No. 09/944,186

Group 2811

Filed September 4, 2001

Examiner Shouxiang Hu

NITRIDE BASED SEMICONDUCTOR  
LIGHT-EMITTING DEVICE

**AMENDMENT**

Assistant Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

May 23, 2005

Sir:

In response to the Office Action mailed January 3, 2005, please amend the above-identified application as follows:

**Amendments to the Claims** are reflected in the listing of claims which begins on page 2 of this paper.

**Remarks** begin on page 7 of this paper.

An **Appendix** is attached following the signature page of this paper.

RAZEGHI is only offered for the teaching of a cavity length above 1 mm and applicants' disclosed prior art is only offered for the teaching of a GaN substrate. Neither RAZEGHI nor the disclosed prior art teaches or suggests what is recited in claim 71. As set forth above, DOMEN et al. do not disclose or suggest what is recited in claim 71. Since claims 75, 78, 80, 122 and 123 depend from claim 71 and further define the invention, the proposed combination of references would not render obvious claims 75, 78, 80, 122 and 123.

In view of the present amendment and the foregoing remarks, it is believed that the present application has been placed in condition for allowance. Reconsideration and allowance are respectfully requested.

Please charge the terminal disclaimer fee of \$130 to Deposit Account No. 25-0120.